

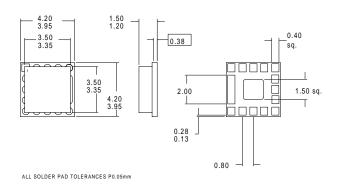
CDMA/TDMA/PACS 1900MHZ 3V POWER AMPLIFIER

Typical Applications

- PACS Handsets and Base Stations
- 3V 1850-1910MHz CDMA PCS Handsets
- 3V 1750-1780MHz CDMA PCS Handsets
- 3V TDMA PCS Handsets
- Spread-Spectrum Systems
- Commercial and Consumer Systems

Product Description

The RF2153 is a high-power, high-efficiency linear amplifier IC targeting 3V handheld systems. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 3V CDMA and TDMA handheld digital equipment, spread-spectrum systems, and other applications in the 1750MHz to 1910MHz band. The device is packaged in a compact 4mmx4mm (LCC). The device's frequency response can be optimized for linear performance in the 1750MHz to 1910MHz band.

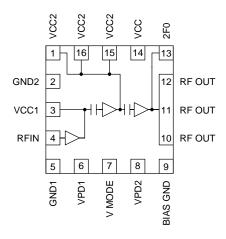


Optimum Technology Matching® Applied

☐ Si BJT
☐ Si Bi-CMOS

▼ GaAs HBT

☐ GaAs MESFET



Functional Block Diagram

Package Style: MP16KO1A

Features

- Single 3V Supply
- 29dBm Linear Output Power
- 30dB Linear Gain
- 33% Linear Efficiency CDMA
- 40% Linear Efficiency TDMA
- On-board Power Down Mode

Ordering Information

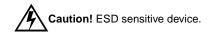
RF2153 CDMA/TDMA/PACS 1900MHz 3V Power Amplifier RF2153 PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc. 7625 Thorndike Road Greensboro, NC 27409, USA Tel (336) 664 1233 Fax (336) 664 0454 http://www.rfmd.com

RF2153

Absolute Maximum Ratings

Rating	Unit
+8.0	V_{DC}
+4.5	V_{DC}
+3.5	V_{DC}
+3.5	V_{DC}
+10	dBm
-30 to +110	℃
-30 to +150	℃
	+8.0 +4.5 +3.5 +3.5 +10 -30 to +110



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Parameter		Specification	1	Unit	Condition
Farameter	Min.	Тур.	Max.	Unit	Condition
Overall - CDMA					T=25°C, V _{CC} =3.4V unless otherwise speci- fied
Usable Frequency Range	1750		1910	MHz	
Typical Frequency Range		1750-1780 1850-1910		MHz MHz	Output Matching Network Tune Output Matching Network Tune
Small Signal Gain	30	32	34	dB	V _{MODE} =Low 0V to 0.5V
	26	29			V _{MODE} =High 2.5V to 3.0V
Linear Gain	26	29		dB	V _{MODE} =High 2.5V to 3V
					P_{OUT} =29dBm, V_{CC} =3.4V, V_{REG} =2.8V
Second Harmonic (including second harmonic trap)		-35		dBc	
Third Harmonic		-40		dBc	
Fourth Harmonic		-45		dBc	
Minimum Linear Output Power (CDMA or TDMA Modulation)	29			dBm	
Idle Current	90	100	200	mA	$V_{MODE} = >2.5 V$
CDMA Linear Efficiency	30	33			P_{OUT} =29dBm, V_{CC} =3.4V, V_{REG} =2.8V
CDMA Adjacent Channel Power Rejection @ 1.25MHz		-46	-44	dBc	P_{OUT} =29dBm, V_{CC} =3.4V, V_{REG} =2.8V
Minimum Linear Output Power (CDMA Modulation)	28	+29		dBm	V _{CC} =3.0 V, V _{REG} =2.8 V
Input VSWR		< 2:1			
Output Load VSWR	10:1				No Damage.
Turn On/Off Time			40	μs	
Overall - TDMA					T=25°C, V _{CC} =3.4V unless otherwise speci-
Lella Commana I		050	500	0	fied
Idle Current	00	250	500	mA	V _{MODE} =0V to 0.5V
TDMA Linear Efficiency	30	40		%	P_{OUT} =30dBm, V_{CC} =3.4V, V_{REG} =2.8V
TDMA ACP @ 30kHz		-29	-28	dBc	P _{OUT} =30dBm
TDMA ALT @ 60kHz		-49	-48	dBc	P _{OUT} =30dBm

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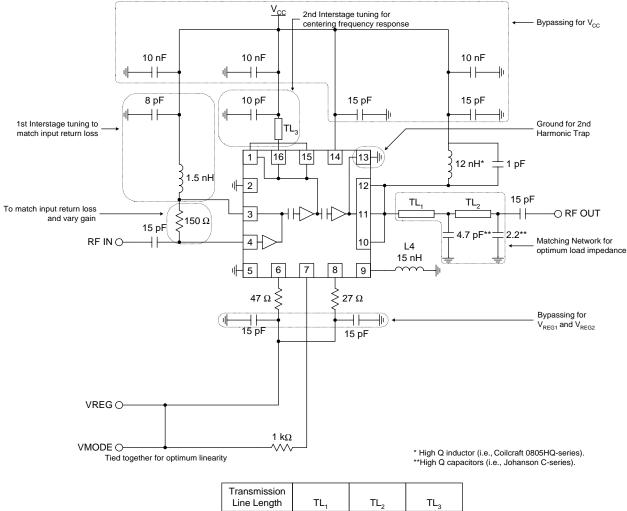
Parameter		Specification			Condition	
Parameter	Min.	Тур.	Max.	Unit	Condition	
Power Supply						
Power Supply Voltage	3.0	3.4	4.5	V		
V _{PD} Current		10		mA	Total pins 6 and 8	
V _{PD} and V _{MODE} Current		11	13	mA	Total pins 6, 7 and 8	
Total Current (Power down)			10	μΑ	$V_{PD} = low$	
V _{PD} "Low" Voltage		0	0.2	V		
V _{PD} "High" Voltage	2.7	2.8	2.9	V		
MODE "High" Voltage	2.5	2.8		V	R1=1kΩ	
MODE "Low" Voltage		0	0.5	V	R1=1kΩ	
Stability		3:1			Inband	
		20:1			Outband	
Spurious		<-60		dBc		
Noise Power		-136		dBm/Hz	@ 80MHz offset	

RF2153

Pin	Function	Description	Interface Schematic
1	VCC2	Power supply for second stage and interstage match. Pins 1, 15 and 16 should be connected by a common trace where the pins contact the printed circuit board.	
2	GND2	Ground for second stage. Keep traces physically short and connect immediately to ground plane for best performance. This ground should be isolated from the backside ground contact on top metal layer.	
3	VCC1	Power supply for first stage and interstage match. V _{CC} should be fed through a 1.5nH inductor terminated with a 15pF capacitor on the supply side.	See pin 4.
4	RF IN	RF input. An external 15pF series capacitor is required as a DC block and also provides for an input VSWR of <2:1 typical.	VCC1 RF IN O From Bias Network GND1
5	GND1	Ground for first stage. Keep traces physically short and connect immediately to ground plane for best performance. This ground should be isolated from the backside ground contact on top metal layer.	See pin 4.
6	VPD1	Power Down control for first and second stages. When this pin is "low", all first and second stage circuits are shut off. When this pin is 2.8V, all first stage circuits are operating normally. V _{PD1} requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V.	
7	VMODE	For full power operation, MODE is set low. VMODE will reduce the bias current by up to 50% when set HIGH. Large Signal Gain is reduced approximately 1.5dB at 29dBm P _{OUT} and Small Signal Gain is reduced approximately 6dB. An external series resistor is optional to limit the amount of current required by the V _{MODE} pin.	
8	VPD2	Power Down control for the third stage. When this pin is "low", the third stage circuit is shut off. When this pin is 2.8 V, the third stage circuit is operating normally. V _{PD} requires a regulated 2.8 V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8 V. A 15pF high frequency bypass capacitor is recommended.	
9	BIAS GND	Requires a 15nH inductor.	
10	RF OUT	RF output and power supply for final stage. This is the unmatched collector output of the third stage. A DC block is required following the matching components. The biasing may be provided via a parallel L-C set for resonance at the operating frequency of 1850MHz to 1910MHz. It is important to select an inductor with very low DC resistance with a 1 A current rating. Alternatively, shunt microstrip techniques are also applicable and provide very low DC resistance. Low frequency bypassing is required for stability.	RF OUT From Bias Network
11	RF OUT	Same as pin 12.	See pin 10.
12	RF OUT	Same as pin 12.	See pin 10.
13	2FO	Second harmonic trap. Keep traces physically short and connect immediately to ground plane. This ground should be isolated from backside ground contact.	
14	VCC	Supply for bias reference and control circuits. High frequency bypassing may be necessary.	
15	VCC2	Same as pin 1.	
16	VCC2	Same as pin 1.	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

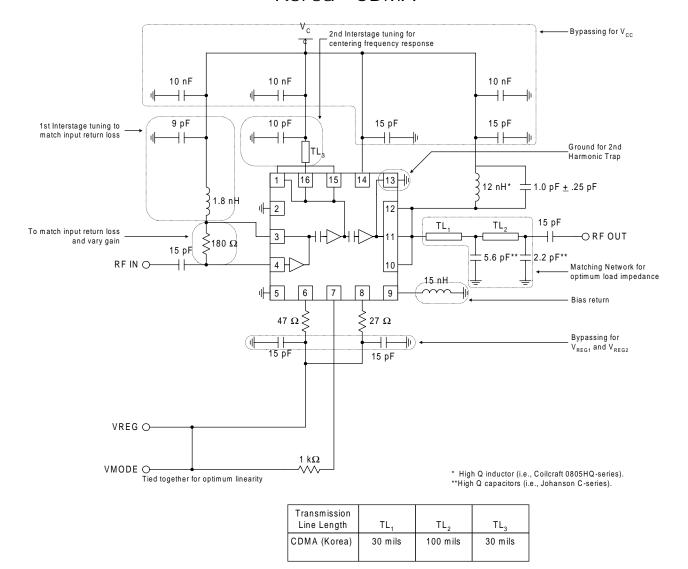
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Application Schematic US - CDMA



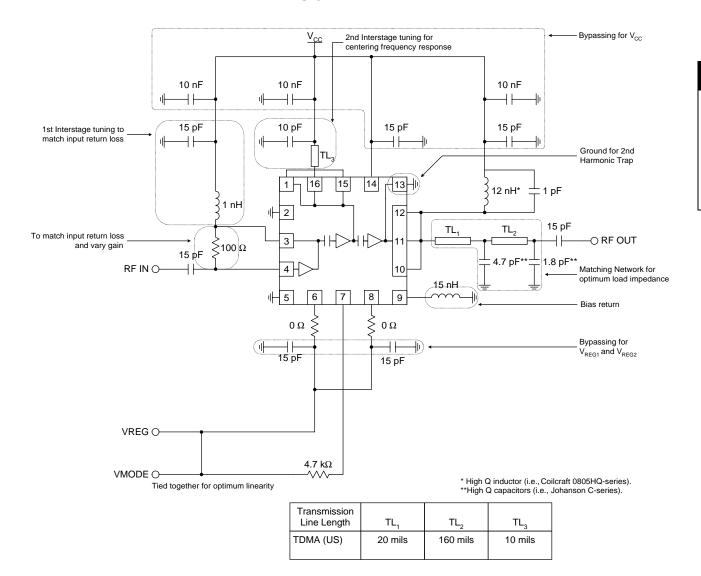
CDMA (US) 20 mils 100 mils 20 mils

Application Schematic Korea - CDMA

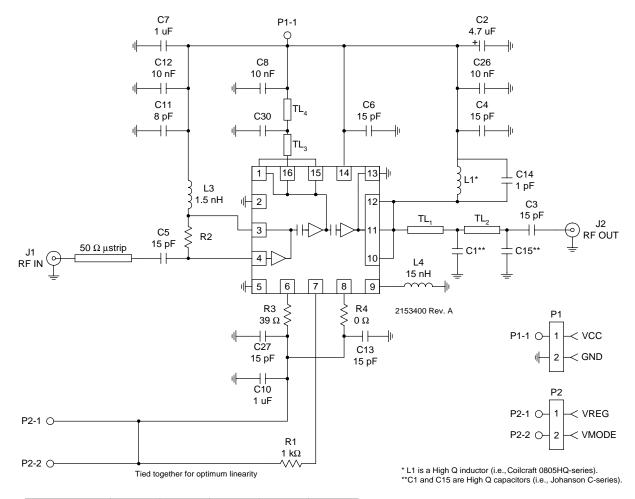


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Application Schematic US - TDMA



Evaluation Board Schematic US - CDMA

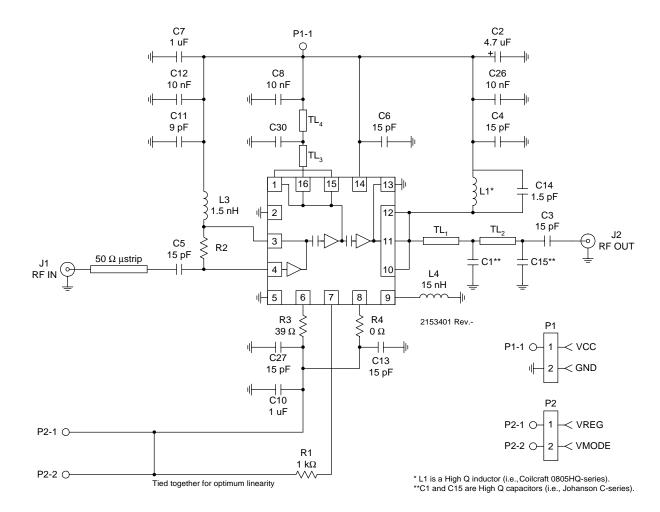


Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C15 (pF)
CDMA (US)	150	10	4.7	12	2.2

Transmission Line Length	TL ₁	TL_2	TL ₃	TL ₄
CDMA (US)	20 mils	100 mils	20 mils	100 mils or ≥ 2.7 nH inductor

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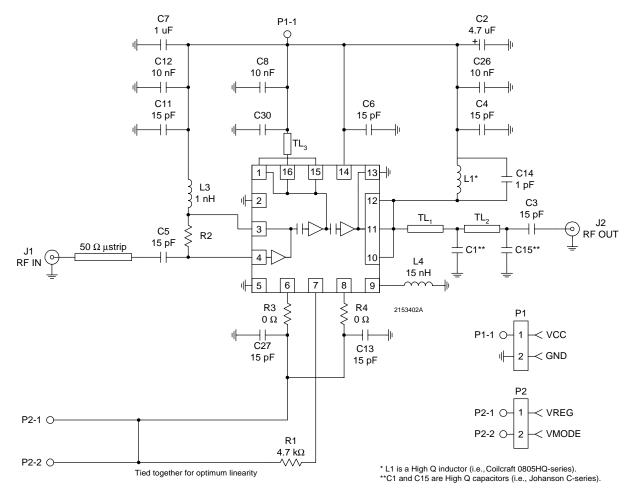
Evaluation Board Schematic Korea - CDMA



Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C15 (pF)
CDMA (Korea)	180	11	5.6	12	2.2

Transmission Line Length	TL ₁	TL ₂	TL ₃	TL ₄
CDMA (Korea)	30 mils	100 mils	30 mils	100 mils or ≥ 2.7 nH inductor

Evaluation Board Schematic US - TDMA



Board	R2 (Ω)	C30 (pF)	C1 (pF)	L1 (nH)	C15 (pF)
TDMA (US)	100	10	4.7	12	1.8

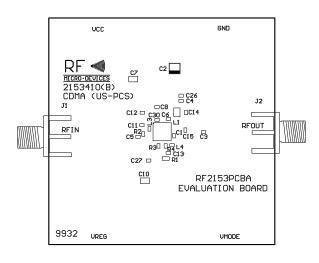
Transmission Line Length	TL ₁	TL_2	TL ₃
TDMA (US)	20 mils	160 mils	10 mils

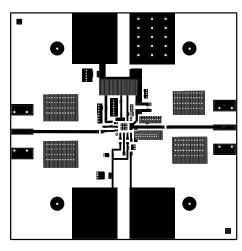
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Evaluation Board Layout US - CDMA

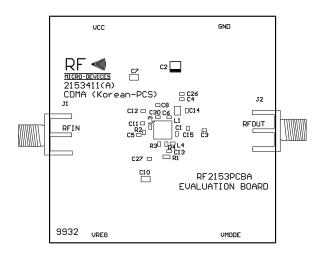
Board Size 2.0" x 2.0"

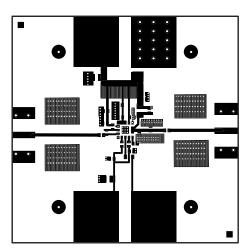
Board Thickness 0.031", Board Material FR-4



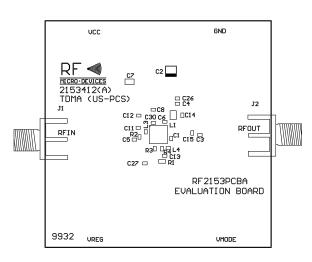


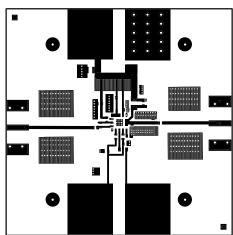
Evaluation Board Layout Korea - CDMA





Evaluation Board Layout US - TDMA





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